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Tunneling Magnetoresistance Sensors for Low Intensity Fields

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Unpatterned magnetic tunnel junctions using compound free layers based on CoFeB, along with NiFe or CoFeBTa were studied magnetically to compare their behaviour in a linear region, with the goal of identifying which would be more adequate for magnetic sensors. These materials were selected with the prospect of obtaining lower coercivity in this linear region while minimizing electrical noise. Similar magnetic behaviour was observed for both, for the same thickness values and more elaborate results would be drawn from an electrical study of these structures after patterning.

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